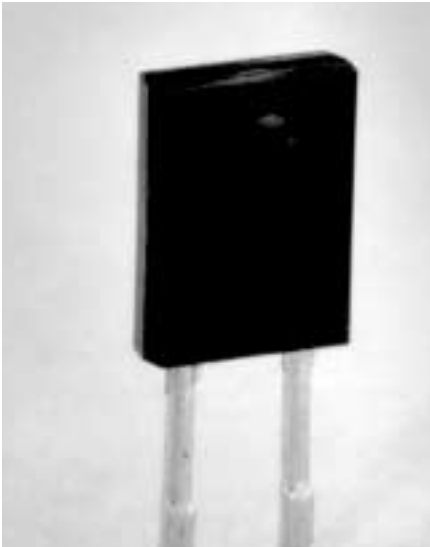


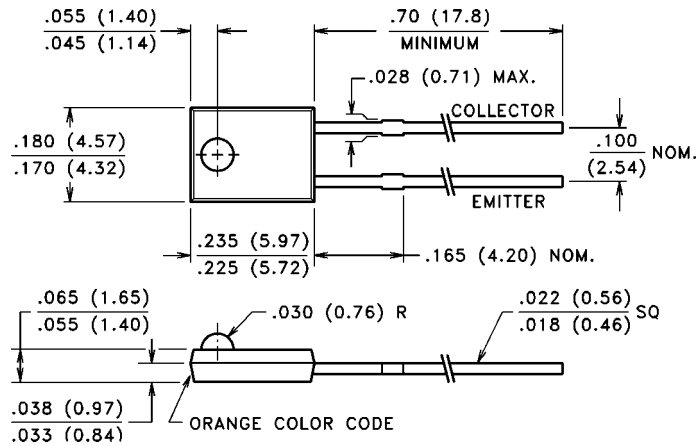
# .025" NPN Phototransistors

IRT Molded Lensed Lateral Package

VTT7222H, 7223H, 7225H



## PACKAGE DIMENSIONS inch (mm)



CASE 7 LATERAL  
CHIP TYPE: 25T

## PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor mounted in a 3 mm diameter, lensed, end looking, plastic package. The package material transmits infrared and blocks visible light. These devices are spectrally and mechanically matched to the VTE717XH series of IREDs.

## ABSOLUTE MAXIMUM RATINGS

(@ 25°C unless otherwise noted)

Maximum Temperatures	
Storage Temperature:	-40°C to 85°C
Operating Temperature:	-40°C to 85°C
Continuous Power Dissipation:	50 mW
Derate above 30°C:	0.71 mW/°C
Maximum Current:	25 mA
Lead Soldering Temperature:	260°C
	(1.6 mm from case, 5 sec. max.)

RoHS Compliant



## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92).

Part Number	Light Current		Dark Current	Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response $\theta_{1/2}$		
	$I_C$		$I_{CEO}$	$V_{BR(CEO)}$	$V_{BR(ECO)}$	$V_{CE(SAT)}$	$t_R/t_F$			
	mA	H fc (mW/cm <sup>2</sup> ) $V_{CE} = 5.0 V$	H = 0	$I_C = 100 \mu A$ H = 0	$I_E = 100 \mu A$ H = 0	$I_C = 1.0 mA$ H = 400 fc	$I_C = 1.0 mA$ $R_L = 100 \Omega$			
	Min.	Max.	(nA) Max.	$V_{CE}$ (Volts)	Volts, Min.	Volts, Min.	Volts, Max.		$\mu sec$ , Typ.	Typ.
VTT7222H	0.9	—	100 (5)	100	10	30	5.0	0.25	2.0	+36°
VTT7223H	1.8	—	100 (5)	100	10	30	5.0	0.25	2.0	+36°
VTT7225H	4.0	—	100 (5)	100	10	30	5.0	0.25	4.0	+36°

Refer to General Product Notes, page 2.